

Cypress Semiconductor Product Qualification Report

QTP# 172504, 172206, 172207 VERSION *D
September, 2018

Microcontrollers with Flash 180nm Technology (CU80F), Cypress FAB25	
CY91F467DA/F467DB CY91F467CB,CY91F467SA CY91F465PA,CY91F467PA CY91F047PMC-GS-UJE1	FR60 32-bit Microcontroller
CY96F906HSBPMCR-GSE2 CY96F918DSBPMC-GS-UJERE2 CY96F386RSC CY96F387RSC	16-bit Proprietary Microcontroller F2MC-16FX
CY90950 Series CY90990 Series CY90F037JDSPMC-GS-UJE1 CY90F039JBSPMC-GS-UJE1 CY90F039YBSPMC-GS-UJE1	16-bit Proprietary Microcontroller F2MC-16LX

FOR ANY QUESTIONS ON THIS REPORT, PLEASE CONTACT
reliability@cypress.com or via a CYLINK CRM CASE

Prepared By:
 Norio Harada
 Reliability Engineer

Reviewed By:
 Kunihiro Miyazono
 Reliability Manager

Approved By:
 David Hoffman
 Reliability Director

PRODUCT QUALIFICATION HISTORY

QTP Number	Description of Qualification Purpose	Date
172504	Qualification of 180nm Technology (CU80F) Microcontroller product family at Fab25	December, 2017
172206 173006	Qualification of Fab25 process with J-Devices Fukuoka Site	December, 2017
172207	Qualification of Fab25 process with J-Devices Usuki Site	December, 2017

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualification of 180nm Technology (CU80F) Microcontroller product family at Fab25	
Marketing Part #:	CY91F467DAPFVS-GS-UJE2
Device Description:	32bit general purpose single-chip products with Flash
Cypress Division:	Microcontroller and Connectivity Division

PACKAGE	ASSEMBLY FACILITY SITE
QFP208	J-Devices Miyagi Site

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	HQB208
Package Outline, Type, or Name:	208-Quad Flat Package (QFP)
Mold Compound Name/Manufacturer:	CEL-9210HFSK / Hitachi
Mold Compound Flammability Rating:	V-0
Mold Compound Alpha Emission Rate:	Alpha1 : 8ppm, Alpha-2 : 35ppm
Lead Frame Material:	Cu Alloy
Substrate Material:	N/A
Lead Finish, Composition / Thickness:	Pure-Sn / 7 – 20um
Die Backside Preparation Method/Metallization:	Si Back Grind
Die Separation Method:	Dicing
Die Attach Supplier:	Hitachi
Die Attach Material:	EN4040
Bond Diagram Designation	F09-HAS-BA-S02123-MLF208QSTH1
Wire Bond Method:	Ultrasonic & Force
Wire Material/Size:	Au / 23um (0.9mil)
Thermal Resistance Theta JA □C/W:	18 degreeC/W
Package Cross Section Yes/No:	Yes
Name/Location of Assembly (prime) facility:	J-Devices Miyagi
MSL LEVEL	3
REFLOW PROFILE	245 degreeC

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	J-Devices Aizu Site

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualification of Fab25 process with J-Devices Fukuoka Site	
Marketing Part #:	CY91F467DAPFVS-GS-UJE2,
Device Description:	32bit general purpose single-chip products with Flash
Cypress Division:	Microcontroller and Connectivity Division

PACKAGE	ASSEMBLY FACILITY SITE
QFP208	J-Devices Fukuoka Site

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	HQB208
Package Outline, Type, or Name:	208-Quad Flat Package (QFP)
Mold Compound Name/Manufacturer:	CEL-9210HFSK / Hitachi
Mold Compound Flammability Rating:	V-0
Mold Compound Alpha Emission Rate:	Alpha1 : 8ppm, Alpha-2 : 35ppm
Lead Frame Material:	Cu Alloy
Substrate Material:	N/A
Lead Finish, Composition / Thickness:	Pure-Sn / 7 – 20um
Die Backside Preparation Method/Metallization:	Si Back Grind
Die Separation Method:	Dicing
Die Attach Supplier:	Hitachi
Die Attach Material:	EN4040
Bond Diagram Designation	F09-HAS-BA-S02123-MLF208QSTH1
Wire Bond Method:	Ultrasonic & Force
Wire Material/Size:	Au / 23um (0.9mil)
Thermal Resistance Theta JA degreeC/W:	18 degreeC/W
Package Cross Section Yes/No:	Yes
Name/Location of Assembly (prime) facility:	J-Devices
MSL LEVEL	3
REFLOW PROFILE	245 degreeC

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	J-Devices Fukuoka Site

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualification of Fab25 process with J-Devices Usuki Site	
Marketing Part #:	CY96F906HSBPMCR-GSE2, CY96F918DSBPMC-GS-UJERE2
Device Description:	16bit general purpose single-chip products with Flash
Cypress Division:	Microcontroller and Connectivity Division

PACKAGE	ASSEMBLY FACILITY SITE
LQFP100 LQFP48	J-Devices Usuki Site

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	LQ1100
Package Outline, Type, or Name:	100-Low Profile Quad Flat Package (LQFP)
Mold Compound Name/Manufacturer:	CEL-9210HFSK / Hitachi
Mold Compound Flammability Rating:	V-0
Mold Compound Alpha Emission Rate:	Alpha1 : 8ppm, Alpha-2 : 35ppm
Lead Frame Material:	Cu Alloy
Substrate Material:	N/A
Lead Finish, Composition / Thickness:	Pure-Sn / 7 – 20um
Die Backside Preparation Method/Metallization:	Si Back Grind
Die Separation Method:	Dicing
Die Attach Supplier:	Hitachi
Die Attach Material:	EN4040
Bond Diagram Designation	F09-HAS-BA-S03430-MLF100LQV21-NW(CY96F906) F09-HAS-BA-S03726-MLF-100LQV21-NW (CY96F918)
Wire Bond Method:	Ultrasonic & Force
Wire Material/Size:	Au / 23um (0.9mil)
Thermal Resistance Theta JA degreeC/W:	18 degreeC/W
Package Cross Section Yes/No:	Yes
Name/Location of Assembly (prime) facility:	J-Devices
MSL LEVEL	3
REFLOW PROFILE	260 degreeC

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	J-Devices Usuki Site

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualification of Fab25 process with J-Devices Usuki Site	
Marketing Part #:	CY90F037JDSPMC-GS-UJE1, CY90F039JBSPMC-GS-UJE1
Device Description:	16bit general purpose single-chip products with Flash
Cypress Division:	Microcontroller and Connectivity Division

PACKAGE	ASSEMBLY FACILITY SITE
LQFP100 LQFP48	J-Devices Usuki Site

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	LQ1100, LQA048
Package Outline, Type, or Name:	48, 100-Low Profile Quad Flat Package (LQFP)
Mold Compound Name/Manufacturer:	EME-G660B / Sumitomo
Mold Compound Flammability Rating:	V-0
Mold Compound Alpha Emission Rate:	Alpha1 : 8ppm, Alpha-2 : 35ppm
Lead Frame Material:	Cu Alloy
Substrate Material:	N/A
Lead Finish, Composition / Thickness:	Sn/Bi / 5 - 20um
Die Backside Preparation Method/Metallization:	Si Back Grind
Die Separation Method:	Dicing
Die Attach Supplier:	Hitachi
Die Attach Material:	EN4040
Bond Diagram Designation	N/A
Wire Bond Method:	Ultrasonic & Force
Wire Material/Size:	Au / 23um (0.9mil)
Thermal Resistance Theta JA degreeC/W:	18 degreeC/W
Package Cross Section Yes/No:	Yes
Name/Location of Assembly (prime) facility:	J-Devices
MSL LEVEL	3
REFLOW PROFILE	260 degreeC

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	J-Devices Usuki Site

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualification of Fab25 process with J-Devices Usuki Site	
Marketing Part #:	CY96F387RWCPMC-GS-UJE2
Device Description:	16bit general purpose single-chip products with Flash
Cypress Division:	Microcontroller and Connectivity Division

PACKAGE	ASSEMBLY FACILITY SITE
LQFP120	J-Devices Usuki Site

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	LQS120
Package Outline, Type, or Name:	120-Low Profile Quad Flat Package (LQFP)
Mold Compound Name/Manufacturer:	EME-G660B / Sumitomo
Mold Compound Flammability Rating:	V-0
Mold Compound Alpha Emission Rate:	Alpha1 : 8ppm, Alpha-2 : 35ppm
Lead Frame Material:	Cu Alloy
Substrate Material:	N/A
Lead Finish, Composition / Thickness:	Pure-Sn / 7 - 20um
Die Backside Preparation Method/Metallization:	Si Back Grind
Die Separation Method:	Dicing
Die Attach Supplier:	Hitachi
Die Attach Material:	EN4040
Bond Diagram Designation	N/A
Wire Bond Method:	Ultrasonic & Force
Wire Material/Size:	Au / 23um (0.9mil)
Package Cross Section Yes/No:	Yes
Name/Location of Assembly (prime) facility:	J-Devices
MSL LEVEL	3
REFLOW PROFILE	260 degreeC

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	J-Devices Usuki Site

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualification of Fab25 process with J-Devices Usuki Site	
Marketing Part #:	CY91F467CBPMC-GS-UJE2, CY91F467SAPMC-GS-UJE2, CY91F047PMC-GS-UJE1 CY91F465PAPMC-GS-UJE1, CY91F467PAPMC-GS-UJE2
Device Description:	16bit general purpose single-chip products with Flash
Cypress Division:	Microcontroller and Connectivity Division

PACKAGE	ASSEMBLY FACILITY SITE
LQFP144 (91F467CB, 91F047) LQFP176 (91F467SA, 91F465PA, 91F467PA)	J-Devices Fukuoka Site

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	LQS144, LQP176
Package Outline, Type, or Name:	144, 176-Low Profile Quad Flat Package (LQFP)
Mold Compound Name/Manufacturer:	EME-G660B / Sumitomo
Mold Compound Flammability Rating:	V-0
Mold Compound Alpha Emission Rate:	Alpha1 : 8ppm, Alpha-2 : 35ppm
Lead Frame Material:	Cu Alloy
Substrate Material:	N/A
Lead Finish, Composition / Thickness:	Pure-Sn / 7 - 20um (91F467CB, 91F467SA) Sn/Bi / 5 - 20um (91F047)
Die Backside Preparation Method/Metallization:	Si Back Grind
Die Separation Method:	Dicing
Die Attach Supplier:	Hitachi
Die Attach Material:	EN4040
Bond Diagram Designation	N/A
Wire Bond Method:	Ultrasonic & Force
Wire Material/Size:	Au / 23um (0.9mil)
Package Cross Section Yes/No:	Yes
Name/Location of Assembly (prime) facility:	J-Devices
MSL LEVEL	3
REFLOW PROFILE	260 degreeC

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	J-Devices Fukuoka Site

RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENTS

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Early Failure Rate	Dynamic Operating Condition, Max. rating Voltage, 125 degreeC, JESD22-A108, AEC-Q100 Test Temperature : Room and Hot	P
High Temperature Operating Life Latent Failure Rate	Dynamic Operating Condition, Max. rating Voltage, 125 degreeC, JESD22-A108, AEC-Q100 Test Temperature : Room, Cold, and Hot (in that order)	P
High Accelerated Saturation Test (HAST)	JEDEC STD 22-A110, 130 degreeC, 85%RH, Max. Rating Voltage, Precondition: JESD22-A113 Moisture Sensitivity Level3 Test Temperature : Room and Hot	P
Unbiased High Accelerated Saturation Test (UHST)	JEDEC STD 22-A118, 130 degreeC, 85%RH, Precondition: JESD22-A113 Moisture Sensitivity Level3 Test Temperature : Room	P
Temperature Cycle	JESD22-A104, Condition C, -65 to 150 degreeC Precondition: JESD22-A113 Moisture Sensitivity Level3 Test Temperature : Room and Hot	P
High Temperature Storage	JESD22-A103: 150 degreeC, Test Temperature : Room and Hot	P
Electrostatic Discharge Human Body Model (ESD-HBM)	AEC-Q100-002 +/- 2000V Test Temperature : Room and Hot	P
Electrostatic Discharge Charge Device Model (ESD-CDM)	AEC-Q100-011 +/- 500V (+/-750V Corner pin) Test Temperature : Room and Hot	P
Static Latch up	AEC-Q100-004 +/- 100mA, 8.25V (125°C) Test Temperature : Room and Hot	P
Endurance + Data Retention	AEC-Q100-005 Endurance (10Kcycling) at 125 degreeC with Retention at 150 degreeC / Operation Life at 125 degreeC, Endurance (10Kcycling) at 25 degreeC with Retention at 55 degreeC,	P
Electrical Distribution	AEC-Q100-009, AEC-Q003 / Cpk > 1.67 Test temperature : Room, Hot, and Cold.	P
Wire Bond Shear (Before stress)	MIL-STD883, Cpk>1.67	P
Wire Bond Pull (Before stress)	MIL-STD883, Cpk>1.67	P
Wire Bond Pull Post Temperature Cycle	MIL-STD883	P
Acoustic Microscopy	JEDEC J-STD-020, Precondition: JESD22-A113 Moisture Sensitivity Level3	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal AF ³	Failure Rate
High Temperature Operating Life Early Failure Rate	3,798 Devices	0	N/A	N/A	0 PPM
High Temperature Operating Life ^{1,2} Long Term Failure Rate	1,192,000 Device Hours	0	0.7	78	9.8 FIT

¹ Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.

² Chi-squared 60% estimations used to calculate the failure rate.

³ Thermal Acceleration Factor is calculated from the Arrhenius equation

$$AF = \exp \left[\frac{E_A}{k} \left[\frac{1}{T_2} - \frac{1}{T_1} \right] \right]$$

where:

E_A = The Activation Energy of the defect mechanism.

K = Boltzmann's constant = 8.62×10^{-5} eV/Kelvin.

T_1 is the junction temperature of the device under stress and T_2 is the junction temperature of the device at use conditions.

Reliability Test Data

QTP #: 172504, 172206, 172207

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS : High Temperature Operation Life (Early Failure Rate)							
CY91F467DA	J4326LP	1541Z01	Miyagi	96	381	0	
CY91F467DA	J4326LP	1541Z02	Miyagi	96	245	0	
CY91F467DA	J4326LP	1541Z03	Miyagi	96	376	0	
CY91F467DA	J4326LP	1541Z04	Miyagi	96	242	0	
CY91F467DA	J4326LP	1541Z05	Miyagi	96	393	0	
CY91F467DA	J4326M8	1541Z06	Miyagi	96	247	0	
CY91F467DA	J4326M8	1541Z07	Miyagi	96	246	0	
CY91F467DA	J4326M8	1541Z08	Miyagi	96	392	0	
CY91F467DA	J4298H9	1541Z09	Miyagi	96	246	0	
CY91F467DA	J4298H9	1541Z10	Miyagi	96	394	0	
CY91F467DA	J4298H9	1541Z11	Miyagi	96	390	0	
CY91F467DA	J4298H9	1541Z12	Miyagi	96	246	0	
STRESS : High Temperature Operation Life (Latent Failure Rate)							
CY91F467DA	J4326LP	1541Z04	Miyagi	2000	80	0	
CY91F467DA	J4326M8	1541Z07	Miyagi	2000	80	0	
CY91F467DA	J4298H9	1541Z12	Miyagi	2000	80	0	
CY91F467DA	J6261JP	1723822	Fukuoka	1000	77	0	
CY91F467DA	J6132VX	1723826	Fukuoka	1000	77	0	
CY91F467DA	J6132XX	1723829	Fukuoka	1000	77	0	
STRESS : High Accelerated Saturation Test							
CY91F467DA	J4326LP	1541Z02	Miyagi	96	80	0	
CY91F467DA	J4326M8	1541Z06	Miyagi	96	80	0	
CY91F467DA	J4298H9	1541Z12	Miyagi	96	80	0	
CY91F467DA	J6261JP	1723822	Fukuoka	96	77	0	
CY91F467DA	J6132VX	1723826	Fukuoka	96	77	0	
CY91F467DA	J6132XX	1723829	Fukuoka	96	77	0	
CY90F906	J6305N0	1723N00	Usuki	96	80	0	
CY90F906	J6305NU	1723N04	Usuki	96	77	0	
CY90F906	J6995NY	1723N08	Usuki	96	77	0	

Reliability Test Data

QTP #: 172504, 172206, 172207

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS : Unbiased High Accelerated Saturation Test							
CY91F467DA	J4326LP	1541Z02	Miyagi	96	80	0	
CY91F467DA	J4326M8	1541Z06	Miyagi	96	80	0	
CY91F467DA	J4298H9	1541Z09	Miyagi	96	80	0	
CY91F467DA	J6261JP	1723822	Fukuoka	96	77	0	
CY91F467DA	J6132VX	1723826	Fukuoka	96	77	0	
CY91F467DA	J6132XX	1723829	Fukuoka	96	77	0	
CY90F906	J6305N0	1723N01	Usuki	96	77	0	
CY90F906	J6305NU	1723N03	Usuki	96	77	0	
CY90F906	J6995NY	1723N06	Usuki	96	77	0	

STRESS ; Temperature Cycle

CY91F467DA	J4326LP	1541Z02	Miyagi	500	80	0	
CY91F467DA	J4326M8	1541Z06	Miyagi	500	80	0	
CY91F467DA	J4298H9	1541Z09	Miyagi	500	80	0	
CY91F467DA	J6261JP	1723822	Fukuoka	500	77	0	
CY91F467DA	J6132VX	1723826	Fukuoka	500	77	0	
CY91F467DA	J6132XX	1723829	Fukuoka	500	77	0	
CY90F906	J6305N0	1723N02	Usuki	500	77	0	
CY90F906	J6305NU	1723N05	Usuki	500	77	0	
CY90F906	J6995NY	1723N06	Usuki	500	77	0	

STRESS ; High Temperature Storage

CY91F467DA	J4326LP	1541Z04	Miyagi	1000	26	0	
CY91F467DA	J4326M8	1541Z07	Miyagi	1000	26	0	
CY91F467DA	J4298H9	1541Z12	Miyagi	1000	26	0	
CY91F467DA	J6261JP	1723822	Fukuoka	1000	45	0	
CY90F906	J6995NY	1723N08	Usuki	1000	45	0	

STRESS ; ESD-HBM

CY91F467DA	J4326LP	1541Z04	Miyagi	COMP	3	0	
CY96F918	J6134J0	1726N00	Usuki	COMP	3	0	
CY90F037	J7262J0	1749N14	Usuki	COMP	3	0	
CY90F039	J731530	1805N00	Usuki	COMP	3	0	
CY96F387	J7397J0	1821N00	Usuki	COMP	3	0	
CY91F467CB	J715680	1810G00	Fukuoka	COMP	3	0	
CY91F467SA	J7353P0	1810G00	Fukuoka	COMP	3	0	
CY91F047	J7324W0	1809G00	Fukuoka	COMP	3	0	
CY91F467PA	J7481A0	1831F01	Fukuoka	COMP	3	0	
CY91F465PA	J746660	1822G00	Fukuoka	COMP	3	0	

Reliability Test Data

QTP #: 172504, 172206, 172207

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS ; ESD-CDM							
CY91F467DA	J4326LP	1541Z04	Miyagi	COMP	3	0	
CY96F918	J6134J0	1726N00	Usuki	COMP	3	0	
CY90F037	J7262J0	1749N14	Usuki	COMP	3	0	
CY90F039	J731530	1805N00	Usuki	COMP	3	0	
CY96F387	J7397J0	1821N00	Usuki	COMP	3	0	
CY91F467CB	J715680	1810G00	Fukuoka	COMP	3	0	
CY91F467SA	J7353P0	1810G00	Fukuoka	COMP	3	0	
CY91F047	J7324W0	1809G00	Fukuoka	COMP	3	0	
CY91F467PA	J7481A0	1831F01	Fukuoka	COMP	3	0	
CY91F465PA	J746660	1822G00	Fukuoka	COMP	3	0	

STRESS ; Static Latch-up

CY91F467DA	J4326LP	1541Z04	Miyagi	COMP	6	0	
CY96F918	J6134J0	1726N00	Usuki	COMP	6	0	
CY90F037	J7262J0	1749N14	Usuki	COMP	6	0	
CY90F039	J731530	1805N00	Usuki	COMP	6	0	
CY96F387	J7397J0	1821N00	Usuki	COMP	6	0	
CY91F467CB	J715680	1810G00	Fukuoka	COMP	6	0	
CY91F467SA	J7353P0	1810G00	Fukuoka	COMP	6	0	
CY91F047	J7324W0	1809G00	Fukuoka	COMP	6	0	
CY91F467PA	J4781A0	1831F01	Fukuoka	COMP	6	0	
CY91F465PA	J746660	1822G00	Fukuoka	COMP	6	0	

STRESS ; Endurance + Data Retention (HT)

CY91F467DA	J6132X0	1641Z04	Miyagi	732	40	0	
CY91F467DA	J6132V0	1641Z12	Miyagi	732	40	0	
CY91F467DA	J6261H0	1714Z02	Miyagi	732	40	0	
CY91F467DA	J4326LP	1541Z02	Miyagi	732	40	0	
CY91F467DA	J4326M8	1541Z07	Miyagi	732	40	0	
CY91F467DA	J 4 298H9	1541Z11	Miyagi	732	40	0	
CY91F467DA	J6132W0	1631Z05	Miyagi	732	80	0	
CY91F467DA	J6132V0	1641Z14	Miyagi	732	80	0	
CY91F467DA	J6261J7	1701Z04	Miyagi	732	80	0	

STRESS ; Endurance + Data Retention (Operation Life)

CY91F467DA	J4326LP	1541Z04	Miyagi	1000	40	0	
CY91F467DA	J4326M8	1541Z07	Miyagi	1000	40	0	
CY91F467DA	J4298H9	1541Z09	Miyagi	1000	40	0	
CY91F467DA	J4326LP	1541Z03	Miyagi	1000	40	0	
CY91F467DA	J4326M8	1541Z08	Miyagi	1000	40	0	
CY91F467DA	J4298H9	1541Z11	Miyagi	1000	40	0	
CY91F467DA	J6132W0	1631Z05	Miyagi	1000	80	0	
CY91F467DA	J6132V0	1641Z14	Miyagi	1000	80	0	
CY91F467DA	J6261J7	1701Z04	Miyagi	1000	80	0	

Company Confidential

A printed copy of this document is considered uncontrolled. Refer to online copy for latest revision.

Reliability Test Data

QTP #: 172504, 172206, 172207

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS ; Endurance + Data Retention (LT)							
CY91F467DA	J4326LP	1541Z04	Miyagi	1000	26	0	
CY91F467DA	J4326M8	1541Z07	Miyagi	1000	26	0	
CY91F467DA	J4298H9	1541Z09	Miyagi	1000	26	0	
CY91F467DA	J4326LP	1541Z03	Miyagi	1000	26	0	
CY91F467DA	J4326M8	1541Z08	Miyagi	1000	26	0	
CY91F467DA	J4298H9	1541Z11	Miyagi	1000	26	0	
CY91F467DA	J6132W0	1631Z05	Miyagi	1000	26	0	
CY91F467DA	J6132V0	1641Z14	Miyagi	1000	26	0	
CY91F467DA	J6261J7	1701Z04	Miyagi	1000	26	0	
STRESS ; Electrical Distributions							
CY91F467DA	J6261JP	1723822	Fukuoka	COMP	30	0	
CY91F467DA	J6132VX	1723824	Fukuoka	COMP	30	0	
CY91F467DA	J6132XX	1723829	Fukuoka	COMP	30	0	
CY96F918	J6134J0	1723N02	Usuki	COMP	30	0	
CY90F037	J7262J0	1749N14	Usuki	COMP	30	0	
CY96F387	J7397J0	1821N00	Usuki	COMP	30	0	
CY91F467CB	J715680	1810G00	Fukuoka	COMP	30	0	
CY91F467SA	J7353P0	1810G00	Fukuoka	COMP	30	0	
CY91F047	J7324W0	1809G00	Fukuoka	COMP	30	0	
CY91F467PA	J7481A0	1831F01	Fukuoka	COMP	30	0	
CY91F465PA	J746660	1822G00	Fukuoka	COMP	30	0	
STRESS ; Wire Bond Pull (Before Stress)							
CY91F467DA	J6261JP	1723822	Fukuoka	COMP	30	0	
CY91F467DA	J6132VX	1723824	Fukuoka	COMP	30	0	
CY91F467DA	J6132XX	1723829	Fukuoka	COMP	30	0	
CY90F906	J6305N0	1723N02	Usuki	COMP	30	0	
CY90F906	J6305NU	1723N04	Usuki	COMP	30	0	
CY90F906	J6995NY	1723N06	Usuki	COMP	30	0	
STRESS ; Wire Bond Shear (Before Stress)							
CY91F467DA	J6261JP	1723822	Fukuoka	COMP	30	0	
CY91F467DA	J6132VX	1723824	Fukuoka	COMP	30	0	
CY91F467DA	J6132XX	1723829	Fukuoka	COMP	30	0	
CY90F906	J6305N0	1723N02	Usuki	COMP	30	0	
CY90F906	J6305NU	1723N04	Usuki	COMP	30	0	
CY90F906	J6995NY	1723N06	Usuki	COMP	30	0	

Reliability Test Data

QTP #: 172504, 172206, 172207

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
<i>STRESS ; Wire Bond Pull Post Temperature Cycle</i>							
CY91F467DA	J6261JP	1723822	Fukuoka	COMP	30	0	
CY91F467DA	J6132VX	1723824	Fukuoka	COMP	30	0	
CY91F467DA	J6132XX	1723829	Fukuoka	COMP	30	0	
CY90F906	J6305N0	1723N02	Usuki	COMP	30	0	
CY90F906	J6305NU	1723N04	Usuki	COMP	30	0	
CY90F906	J6995NY	1723N06	Usuki	COMP	30	0	

STRESS ; Acoustic Microscopy

CY91F467DA	J6261JP	1723822	Fukuoka	COMP	22	0	
CY91F467DA	J6132VX	1723826	Fukuoka	COMP	22	0	
CY91F467DA	J6132XX	1723829	Fukuoka	COMP	22	0	
CY90F906	J6305N0	1723N00	Usuki	COMP	22	0	
CY90F906	J6305NU	1723N04	Usuki	COMP	22	0	
CY90F906	J6995NY	1723N08	Usuki	COMP	22	0	

Document History Page

Document Title: QTP#172504 Microcontrollers with Flash, 180nm Technology (CU80F), Cypress FAB25
Document Number: 002-22508

Rev.	ECN No.	Orig. of Change	Description of Change
**	6000639	KUMI	Initial release.
*A	6035471	KUMI	Corrected typo. (ASSECLY TO ASSEMBLY)
*B	6137007	KUMI	Add additional qualified product data (CY90F037JDSPMC-GS-UJE1, CY90F039JBSPMC-GS-UJE1), Added wire diameter by 'mil'
*C	6221719	KUMI	Add test temperature, Electrical Distributions, Endurance test result, CY91F467DAPFVS-GS-UJE2 changed to CY91F467DA Added CY91F467CB, CY91F467SA, CY91F047, CY96F386RSC, CY96F387RSC qual result Document title change
*D	6316333	KUMI	Add CY91F465PA, CY91F467PA qualification result.